PROCESS CP307

Small Signal Transistor

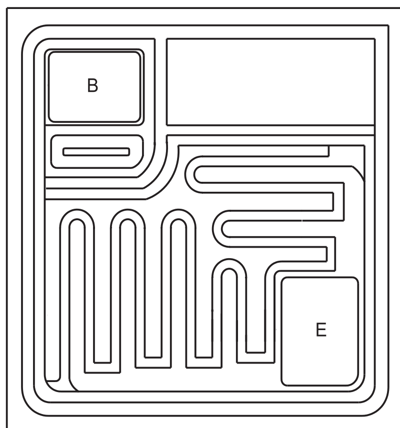
NPN - Silicon Darlington Transistor Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	27 x 27 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	5.3 x 3.8 MILS
Emitter Bonding Pad Area	5.3 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER
15,440

PRINCIPAL DEVICE TYPES
2N6426
2N6427
CMPT6427
CMPTA13
CMPTA14
CXTA14
CZTA14
MPSA13
MPSA14

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R3 (1-August 2002)

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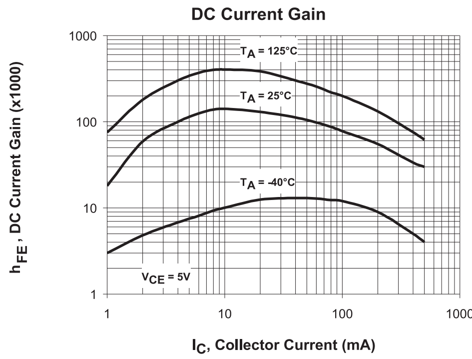
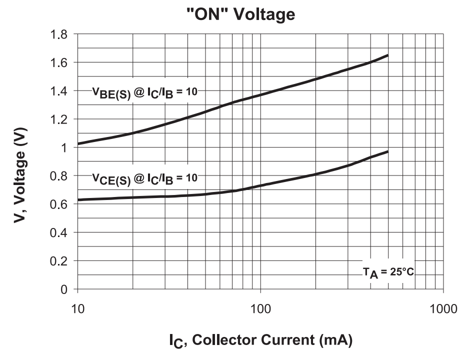
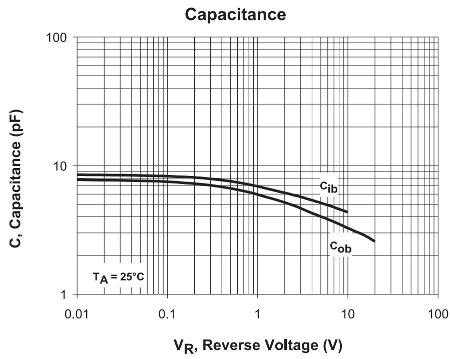
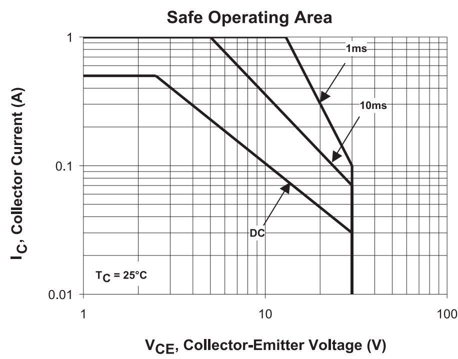
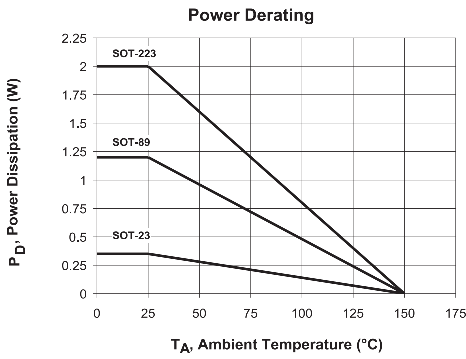
Typical Electrical Characteristics

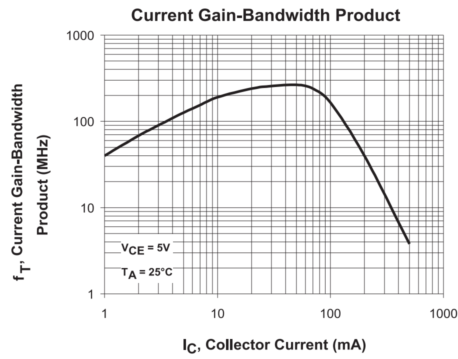












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